EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"6299696".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/13 14:10
L2	79069	(wafter semiconductor substrate) and (shutter separation plate) with (slits holes)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/13 14:27
L3	690	2 and "134".clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/13 14:27
L4	452	(shutter or disc or baffle or plate) with (holes or vent or slits or exhaust) and (semiconductor or wafer or substrate) and (clean adj2 dry)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/13 14:28
L5	2	"5524361".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/13 14:35
L6	2	"20030159718"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/13 14:50
S1	2	"6299696".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/10 16:52
S2	2	"5524361".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/10 16:53
83	10	("20030159718" "5226056" "5524361" "6068002" "6299696").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/10 16:53
S4	564426	(substrate or semiconductor) and holes	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/10 17:28

S5	3636	(substrate or semiconductor) and holes same dry\$3 with gas\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/10 17:28
S6	836	S5 and dry\$3.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/10 17:29
S7	746	134/61	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/11 11:18
S8	4363	134/2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/11 11:18
S9	44	yi adj hun\$jung.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/11 11:18
S10	32	park adj sang-oh.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/11 11:18
S11	163153	(water semiconductor substrate) and (shutter separation plate) with (slit hole)	US-PGPUB; USPAT; USOOR; EPO; JPO; DERWENT	OR	ON	2008/12/11 11:19
S12	163153	(water or semiconductor or substrate) and (shutter or separation or plate) with (slit or hole)	US-PGPUB; USPAT; USOOR; EPO; JPO; DERWENT	OR	ON	2008/12/11 11:20
S13	153	S8 and (shutter plate) with (hole vent slit)	US-PGPUB; USPAT; USOOR; EPO; JPO; DERWENT	OR	ON	2008/12/11 11:21
S14	153	S8 and (shutter plate) with (holes vent slit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/11 11:21
S15	156	S8 and (shutter baffle plate) with (holes vent slit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/11 11:21
S16	284	(cleaning with drying with apparatus) and (shutter baffle plate) with (holes vent slits) and (semiconductor wafer substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/11 11:22

S17	2092	plate) with (holes vent slits exhaust) and	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/12/11 11:22
		substrate) and clean\$3 near5 dry\$3	JPO, DENVENT			***************************************

^{12/13/2008 2:54:02} PM

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